

Valeri Dzhurkov

List of Publications by Year in descending order

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Version: 2024-02-01

15
papers

71
citations

1478505

6
h-index

1588992

8
g-index

15
all docs

15
docs citations

15
times ranked

111
citing authors

#	ARTICLE	IF	CITATIONS
1	Surface modification and chemical sensitivity of sol gel deposited nanocrystalline ZnO films. Materials Chemistry and Physics, 2018, 209, 165-171.	4.0	18
2	Application of Metal-Oxide-Semiconductor structures containing silicon nanocrystals in radiation dosimetry. Open Physics, 2015, 13, .	1.7	8
3	Spectroscopic studies of SiO _x films irradiated with high energy electrons. Journal of Physics: Conference Series, 2014, 558, 012045.	0.4	7
4	Structural, compositional and electrical characterization of Si-rich SiO _x layers suitable for application in light sensors. Materials Science in Semiconductor Processing, 2015, 37, 229-234.	4.0	7
5	High energy electron-beam irradiation effects in Si-SiO _x structures. Journal of Physics: Conference Series, 2016, 682, 012012.	0.4	7
6	UV Sensitivity of MOS Structures with Silicon Nanoclusters. Sensors, 2019, 19, 2277.	3.8	7
7	Phase characterization and ethanol adsorption in TiO ₂ nanotubes anodically grown on Ti6Al4V alloy substrates. Journal of Alloys and Compounds, 2019, 798, 394-402.	5.5	5
8	Selective photosensitivity of metal-oxide-semiconductor structures with SiO _x layer annealed at high temperature. Journal of Materials Science: Materials in Electronics, 2020, 31, 17412-17421.	2.2	3
9	Electrical conductivity and optical properties of tellurium-rich Ge-Sb-Te films. Journal of Physics: Conference Series, 2014, 558, 012046.	0.4	2
10	Room temperature sensitivity of ZnSe nanolayers to ethanol vapours. Journal of Physics: Conference Series, 2019, 1186, 012023.	0.4	2
11	Investigation of resistive switching in SiO ₂ layers with Si nanocrystals. Journal of Physics: Conference Series, 2019, 1186, 012022.	0.4	2
12	UV Dosimeters Based on Metal-Oxide-Semiconductor Structures Containing Si Nanocrystals. Sensor Letters, 2015, 13, 561-564.	0.4	2
13	MOS Structures Containing Si Nanocrystals for Applications in UV Dosimeters. Key Engineering Materials, 0, 605, 380-383.	0.4	1
14	Photoluminescence from 20 MeV electron beam irradiated homogeneous SiO _x and composite Si-SiO _x films. Journal of Physics: Conference Series, 2016, 764, 012018.	0.4	0
15	Resistive switching behavior of SiO _x layers with Si nanoparticles. Journal of Physics: Conference Series, 2017, 794, 012018.	0.4	0